

Title (en)

METHOD FOR MAKING A DEVICE COMPRISING LAYERS OF PLANES OF QUANTUM DOTS

Title (de)

HERSTELLUNGSVERFAHREN FÜR EIN BAUELEMENT BESTEHEND AUS EINEM STAPEL VON QUANTENPUNKT-SCHICHTEN

Title (fr)

PROCEDE DE REALISATION D'UN DISPOSITIF COMPRENANT UN EMPILEMENT DE PLANS DE BOITES QUANTIQUES

Publication

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Application

**EP 00953226 A 20000711**

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Abstract (en)

[origin: FR2797093A1] The invention concerns a method for forming on a Ge or Si monocrystalline substrate successive Si/Ge, Si/SiGe or Si/SiGe/Ge layers for a Ge substrate and inversely for a Si substrate, and the electrochemical treatment of the stack of layers to make the layers porous and form therein residual crystallites. The invention is applicable to devices comprising layers of planes of quantum drops.

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